

1. (Twice Amended) A method of generating ions, comprising:

heating an ion source material composed of indium monoiodide (InI) whose particle size is generally larger than a diameter of an oven nozzle and in a range of heating temperature to produce a desired an ion beam current effective to generate vapor of said indium monoiodide (InI); and

generating indium (In) ions by discharging said vapor.

--21. (New) The method according to claim 1, wherein said heating an ion source material comprises heating said indium monoiodide (InI) in said temperature range of not lower than 300°C and not higher than 380°C to produce said desired ion beam effective to generate said vapor of said indium monoiodide (InI).

22. (New) A method of generating ions, comprising: ✓

heating an ion source material composed of indium monoiodide (InI), to generate vapor of said indium monoiodide (InI); and

generating indium (In) ions by discharging said vapor in an arc chamber, wherein a filament is provided on one side surface of said arc chamber, and a reflecting counter electrode is provided on another side surface of said arc chamber opposite to said one side surface.

23. (New) A method of generating ions, comprising: ✓

heating an ion source material composed of indium monoiodide (InI), to generate vapor of said indium monoiodide (InI); and

generating indium (In) ions by discharging said vapor in an arc chamber, wherein two gas inlets for an inert gas and said vapor are provided on a same face of the arc

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